

Solid-State Drive 2

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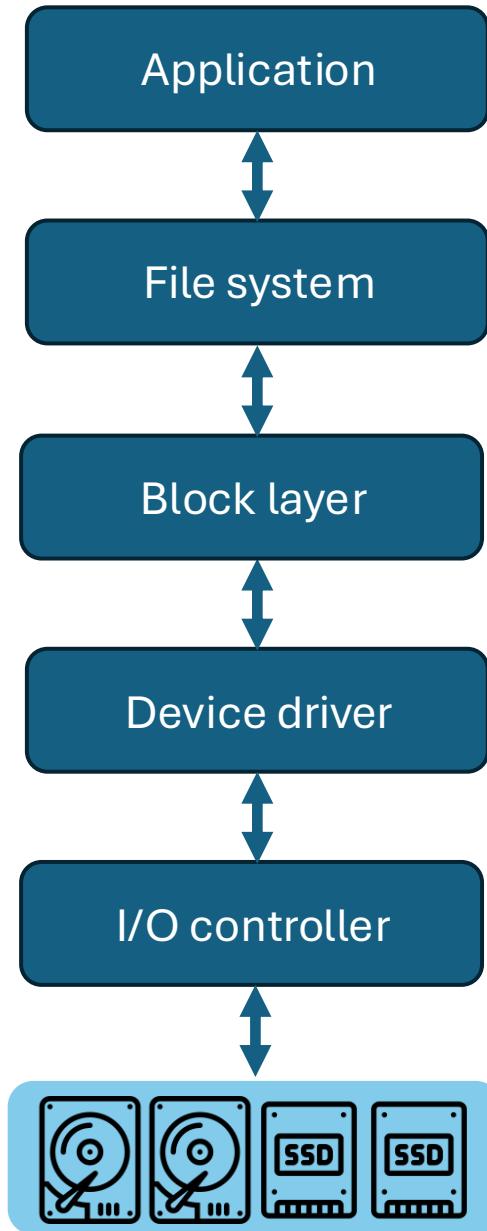


Recap: Solid State Drive

- Why SSD is better than HDDs
- SSD internals
 - how NAND cell works
 - why it wears out
 - different flash cells, e.g., SLC, MLC, TLC, QLC
 - flash translation layer (FTL) functions
 - mapping
 - garbage collection
 - wear leveling

Today

- SSD performance
- SSD reliability
- SSD density
- SSD cost and market
- Future trend



SSD performance

SSD internal parallelism

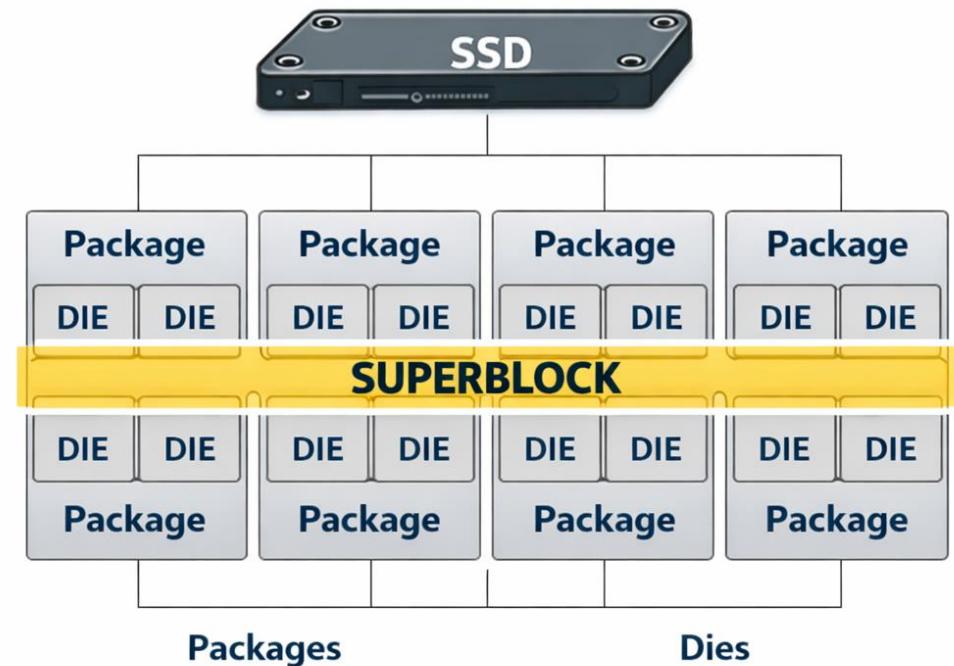
- Channel
 - a NAND interface on the SSD controller
 - electrically, a shared bus for command/address/data and control signals
 - way: the number of independently-selectable NAND targets per channel
 - e.g., an 8-ways channel connects to 8 packages
- A channel connects to multiple packages, and each package is connected to one channel
 - multiple channels avoid the channel becoming a bottleneck
 - read is serviced from the channel(s) where data reside
 - write can be placed across channels (striped)

SSD internal parallelism: hierarchical organization

- Channel and way parallelism
 - read / write to multiple packages / chips simultaneously
 - most important
- Die interleaving
 - pipeline operations within package
 - async die operations: channel bus is faster than die operations
- Plane parallelism: limited

SSD internal parallelism: superblock

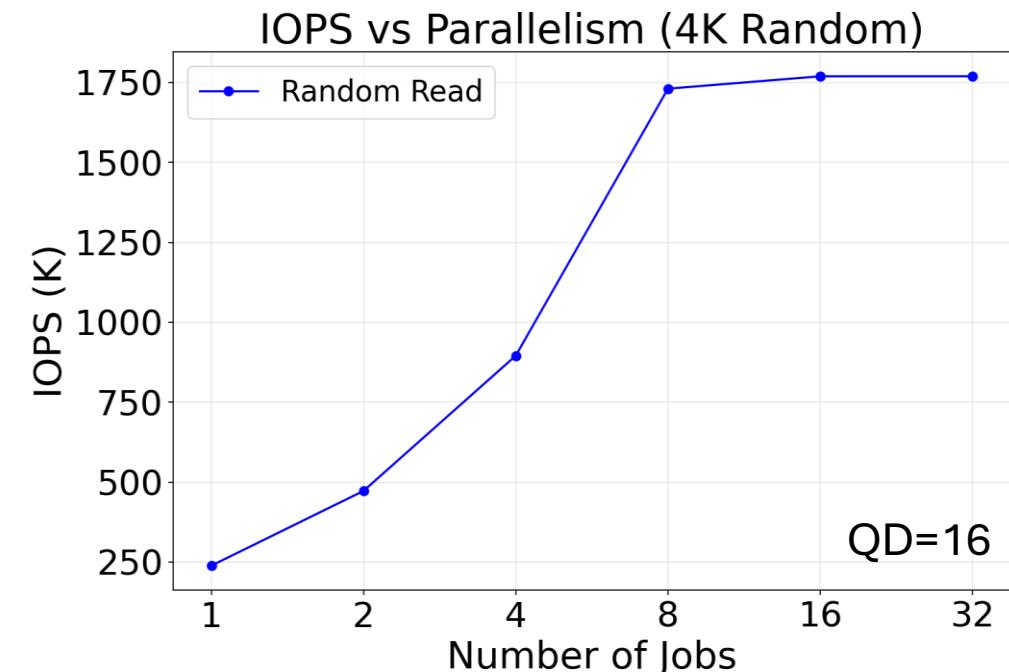
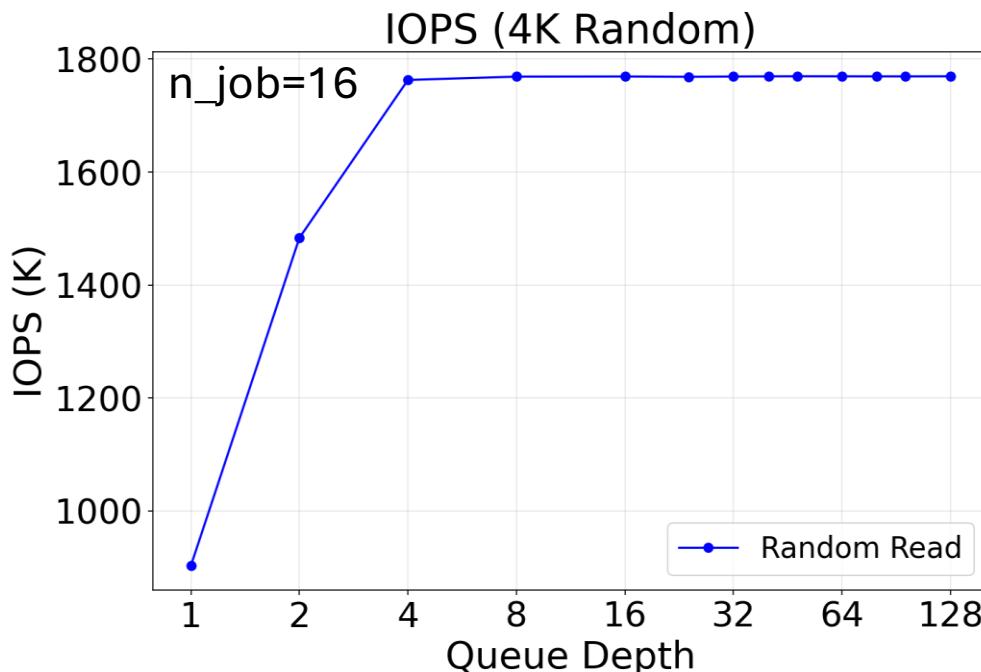
- Parallelism (striping)
 - logical grouping of physical blocks across packages and dies that allow them to be **written and erased simultaneously**
- Reliability
 - use one block for parity (die-level RAID)
- Caveat
 - controller treat as one unit
 - GC penalty: update a 4 KB page requires more copies (write amplification)



Note: this is different from file system superblock

SSD performance: bandwidth and IOPS

- Peak performance requires high concurrency
 - job: multiple proc to leverage queues and channels
 - queue depth: fill the pipeline and fully leverage parallelism



SSD performance: bandwidth and IOPS

- Write cliff: **Why?**
- Cause 1: running out of empty blocks
 - trigger blocking GC
- Cause 2: pSLC caching
 - treat a portion of TLC/QLC as SLC-mode cache for burst writes
 - when cache fills, writes fall back to native TLC/QLC speed (100s MB/s)
- Write performance therefore depends on workload and free space
- SSD expected sustained write bandwidth can be calculated using endurance
 - 1 TB TLC at 2000 PE and 5-year lifetime: $1 \text{ TB} * 2000 / (5 * 365 * 24 * 3600\text{s}) = 12 \text{ MB/s}$

SSD performance: latency

- Page read: 10s μ s
 - lower than mechanical disks (10 ms), but higher than DRAM (10s ns)
- Page program: 100s μ s
- Block erase: 1s ms
- Latency increases from SLC to QLC
 - harder to read, retry and error correction, *every extra bit doubles the latency*
 - harder to program, write latency increases more than read
- The latency above is for SSD medium
 - system level: read is 10-100s μ s, write is shorter due to DRAM buffer
 - tail latency is more useful, but not always determined by device

Comparing NAND cell types

Cell Type	Bits / Cell	Read latency	Write latency	True read bandwidth (MB/s)	True write bandwidth (MB/s)	P/E cycles (Endurance)	Approx. cost (Rel.)
SLC	1	~25 µs	~250 µs	7,000 – 14,000	10,000+	50,000 – 100,000	Very High (5x–10x TLC)
MLC	2	~50 µs	~900 µs	5,000 – 10,000	~2,000	3,000 – 10,000	High (2x–3x TLC)
TLC	3	~75 µs	~1,500 µs	3,000 – 7,000	~800	1,000 – 3,000	Medium (Baseline)
QLC	4	~120 µs	~3,000 µs	1,500 – 4,000	~80-160	100 – 1,000	Low (0.6x–0.8x TLC)
PLC	5	~250+ µs	~5,000+ µs	500 – 1,000	~10-40	<100	Very Low (expected)

SSD reliability

SSD reliability overview

- More reliable than HDDs
 - no mechanical component
 - not susceptible to vibration
 - Uncorrectable Bit Error Rate (UBER): 1-2 order lower than HDD
 - AFR: half of HDD based on BackBlaze report*
- However, when SSDs dies
 - not recoverable

SSD failure modes

- NAND failure modes
 - wear out: P/E cycling
 - data retention loss: charge leakage over time (increase with wear and temperature)
 - read / program disturb: change the threshold distribution of adjacent cells
 - bad blocks: from manufacturing
- Firmware bug
- Controller, DRAM hardware failure: rare

Mitigation

- Over-provisioning
 - wear out and bad block
- Error correction code (ECC)
 - NAND stores parity in OOB/spare area
 - detect and correct errors during read
- Read-retry
- Refresh: prevent data retention loss

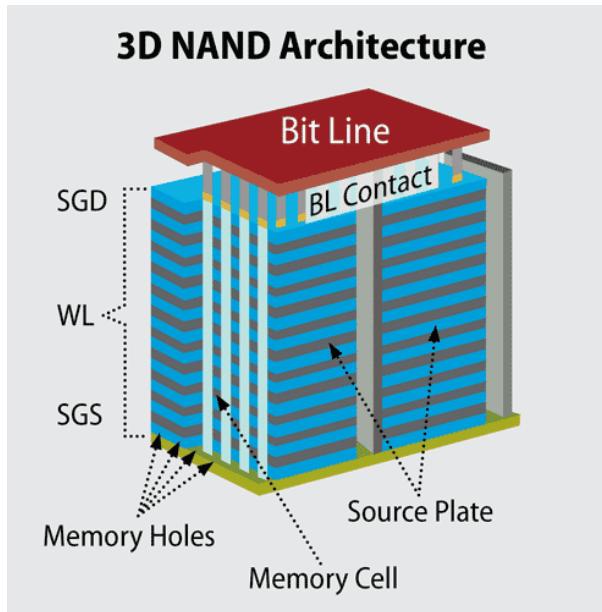
Endurance

- SSDs have limited endurance
 - 1 TB of TLC SSD only support 12 MB/s sustained write
- How do we measure endurance?
- TBW: TB written
- DWPD: disk write per day
 - consumer: 0.1–0.3
 - enterprise: 0.3 (read intensive)–3 (write intensive)
 - DWPD 0.3 allows users to write < 4MB/s per TB, lower than HDDs

SSD Density

SSD density

- Cell size: Moore's law
- More bits per cell:
 - diminishing return
 - SLC->MLC: 100%
 - MLC->TLC: 50%
 - TLC->QLC: 33%
 - QLC->PLC: 20%



3D NAND: 2D -> 3D

- view layer as one floor
- read operation: controller selects one **Bit Line** (column) and one **Word Line** (floor), pinpointing a single cell in the 3D matrix
- modern drives: 300+ layers

Metric	2D (Planar) NAND	3D NAND
Scaling Direction	Horizontal (x, y)	Vertical (z)
Capacity Limit	~128 Gb per die	2 Tb+ per die (and rising)
Endurance	Low (tiny cells)	Higher (larger, more stable cells)
Cost per GB	High (stalled scaling)	Low (scaling via layering)

SSD Cost and Market

SSD cost and market

Component	Cost Share (Approx.)	Function
NAND Flash	70% – 85%	Storage media
DRAM Cache	5% – 10%	Mapping table & write buffer
Controller	5% – 8%	CPU, ECC Engine, PCIe PHY
PCB & others	~5%	Board, capacitors (PLP)
Assembly & Test	~2%	Packaging, Burn-in testing

To reduce cost: reduce DRAM and lower NAND cost

- Global Market Size (2025): ~\$61.3 Billion
- Projected Growth: CAGR of ~16–18% through 2030
- Key Shift: In 2026, Enterprise SSDs are projected to overtake Client SSDs to become the largest segment of the NAND market by revenue.

SSD market segmentation

- **Enterprise / Data Center:** hyper-growth due to data gravity
- **Consumer:** stagnant and low growth due to softened PC demand

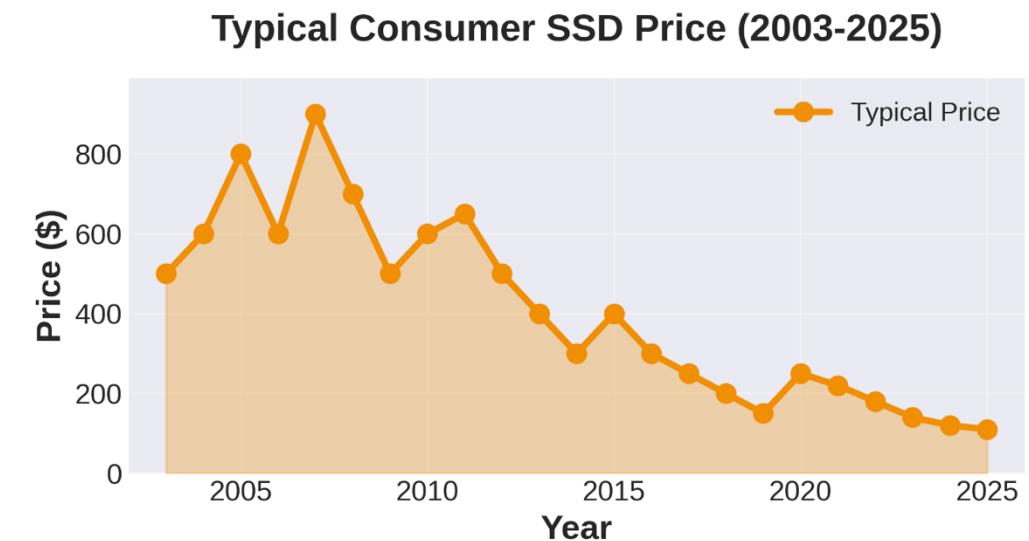
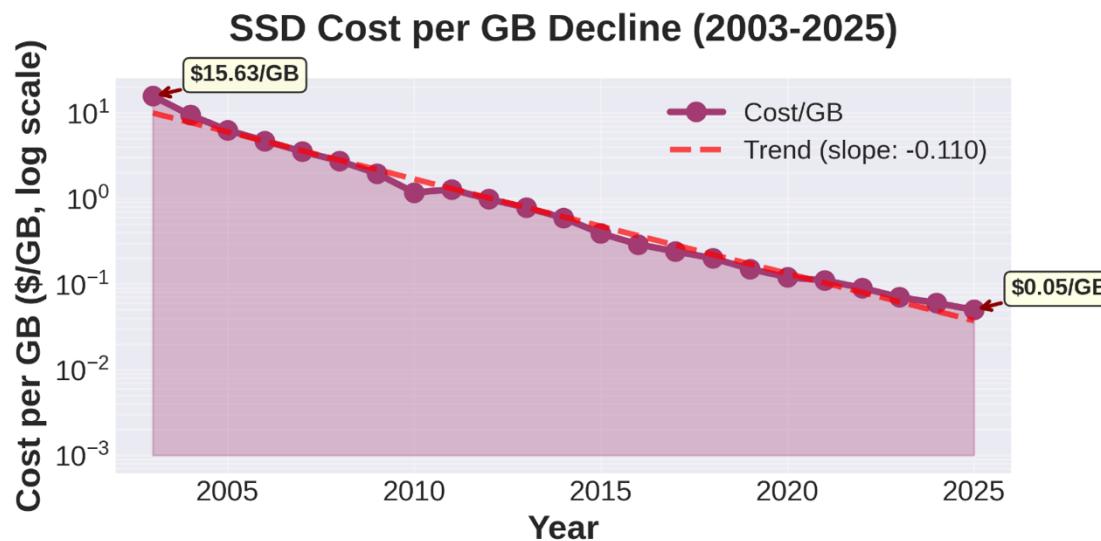
Manufacturer	Market Share (2025)	Strategy & Strength
Samsung	~32%	Volume Leader. Dominates both Client and Enterprise
SK Hynix / Solidigm	~24%	The QLC King. Solidigm (formerly Intel NAND) holds a unique lead in ultra-high capacity (60TB+) QLC drives
Kioxia (Toshiba)	~15%	Mobile Focused. Strong in smartphones (iPhone storage)
Micron	~11%	Often first to market with the highest layer counts

Note: not all manufacturers produce both NAND and controller

Trend

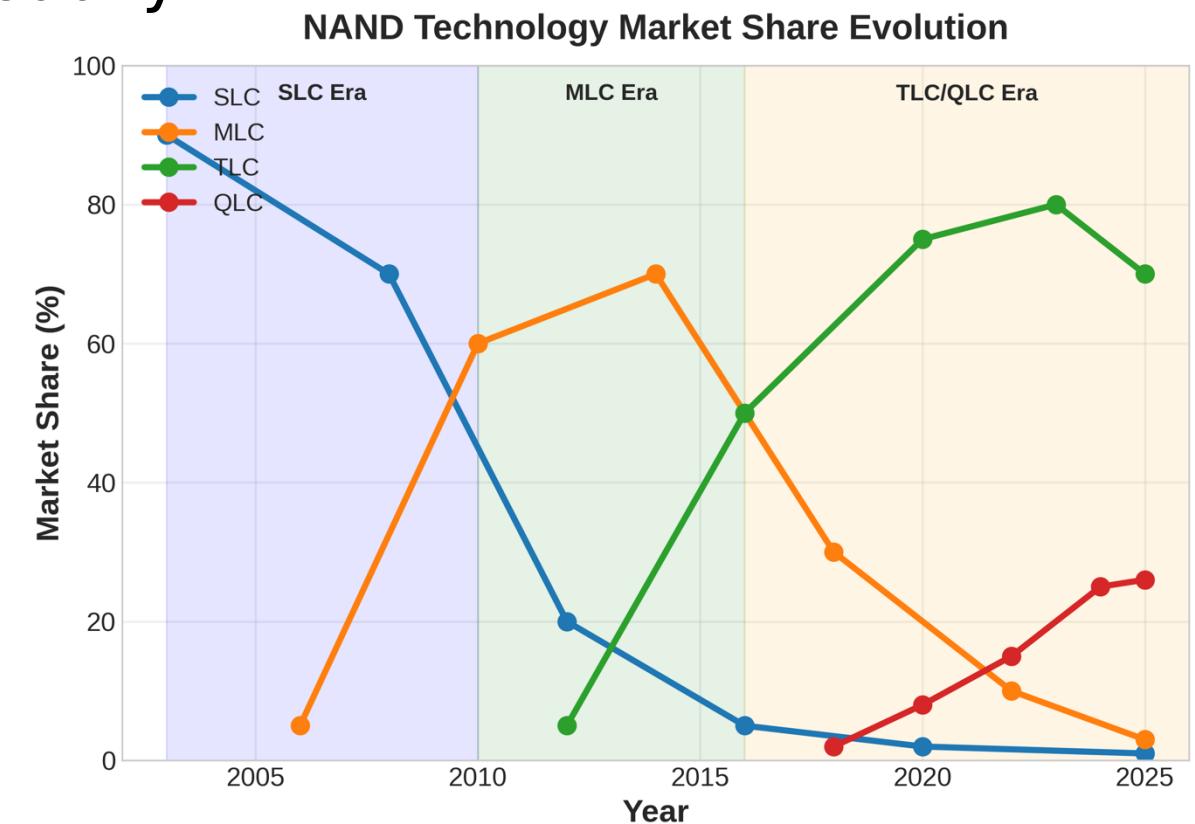
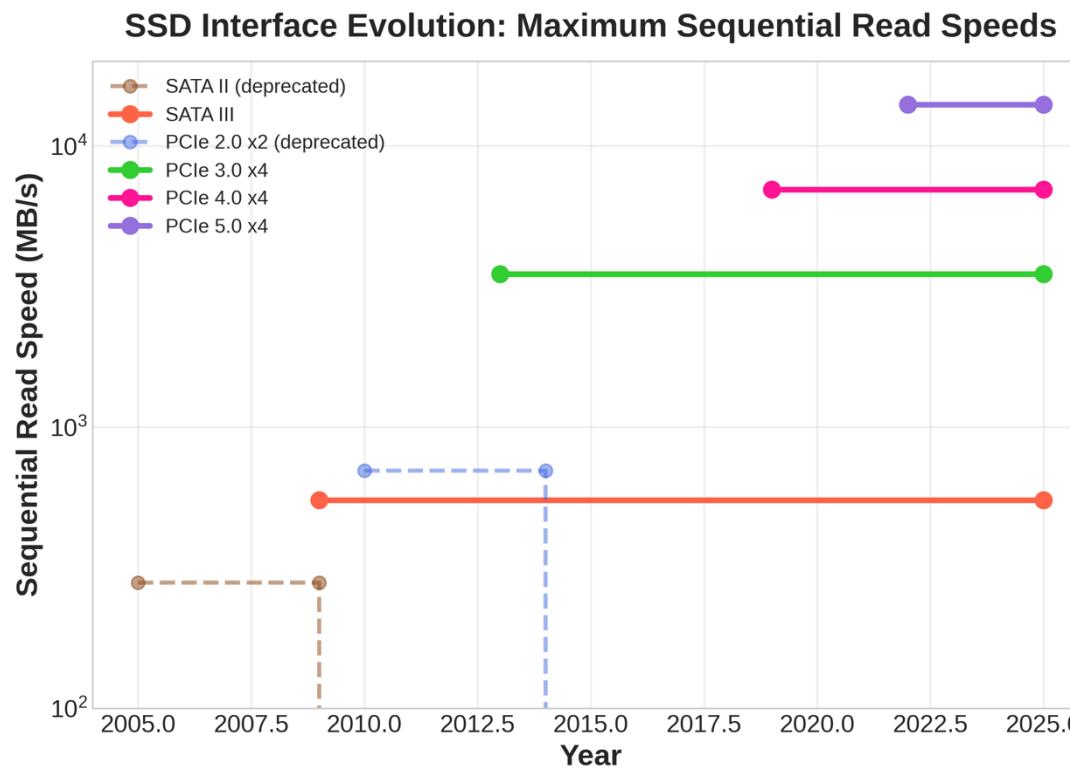
Historical trend

- Density improves close to exponentially



Historical trend

- Bandwidth is always close to interface speed
- Latency has been decreasing steadily



Future trend

- Denser flash
 - more bits per cell, will we have PLC or HLC? **Doubtful**
 - 3D NAND more layers **Yes!**
- Lower latency? **Doubtful**
 - we are already at ~10 µs, other components (software, PCIe, controller) will become bottleneck
- Higher bandwidth? **Yes!**
 - more parallelism, controller and interface improvement
- More IOPS? **Yes!** (same)
- Better power efficiency? **Yes!**

Future trend: implications

- Increasing enterprise adoption for
 - performance
 - physical footprint
 - sustainability (high-density QLC)
- Bandwidth gap between SSDs and DRAM narrows
 - many data can be offloaded to SSDs
 - but what should we do with limited endurance?
- Latency is increasingly lower
 - kernel I/O path has become the bottleneck

Summary

- SSD internal
 - NAND flash physics
 - SLC/MLC/TLC/QLC
 - internal organization
- SSD controller
 - FTL: mapping, garbage collection
- SSD performance
 - high bandwidth and IOPS through internal parallelism
- SSD reliability and SSD density

Three key questions

- What is Flash Translation Layer and what does it do?
- What is SSD's performance characteristics and Why?
- How should you extend SSD lifetime?

Next time

- Block layer
- Interface and protocols
- Device driver
- I/O controller